

**SEMICONDUCTOR
TECHNICAL DATA**

KTA2017
EPITAXIAL PLANAR PNP TRANSISTOR

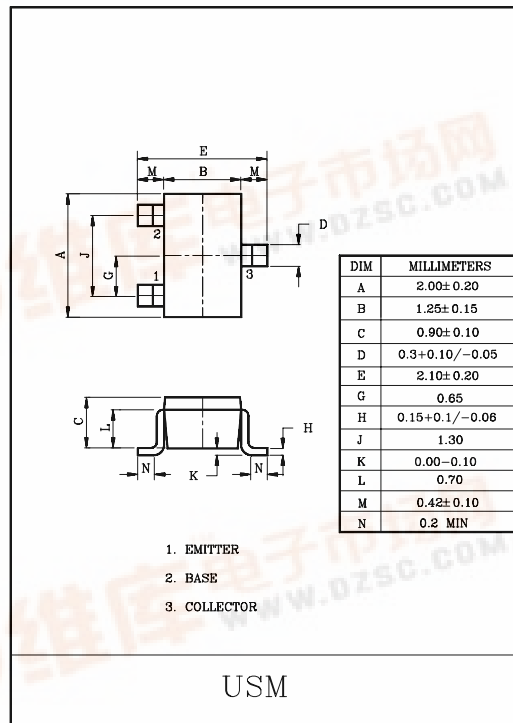
LOW NOISE AMPLIFIER APPLICATION.

FEATURES

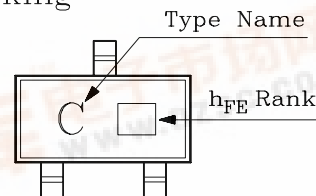
- High Voltage : $V_{CEO}=-120V$.
- Excellent h_{FE} Linearity
: $h_{FE}(0.1mA)/h_{FE}(2mA)=0.95(Typ.)$.
- High h_{FE} : $h_{FE}=200\sim 700$.
- Low Noise : $NF=1dB(Typ.)$, $10dB(Max.)$.
- Complementary to KTC4077.

MAXIMUM RATINGS ($T_a=25^{\circ}C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-120	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-100	mA
Base Current	I_B	-20	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55~150	$^{\circ}C$



Marking



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$)

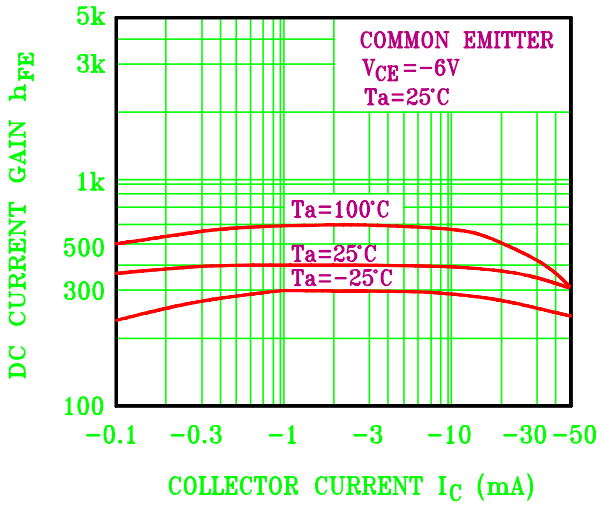
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-120V, I_E=0$	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$	-	-	-0.1	μA
DC Current Gain	h_{FE} (Note)	$V_{CE}=-6V, I_C=-2mA$	200	-	700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-1mA$	-	-	-0.3	V
Transition Frequency	f_T	$V_{CE}=-6V, I_C=-1mA$	-	100	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	4.0	-	pF
Noise Figure	NF	$V_{CE}=-6V, I_C=-0.1mA$ $f=1kHz, R_g=10k\Omega$	-	1.0	10	dB

Note : h_{FE} Classification GR(6):200~400 BL(8):350~700

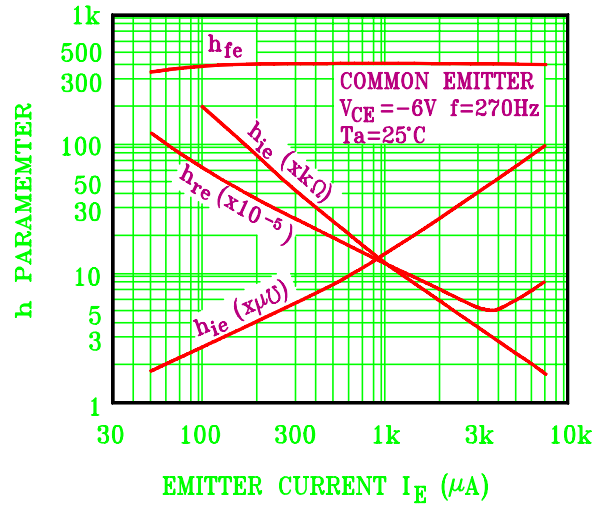


KTA2017

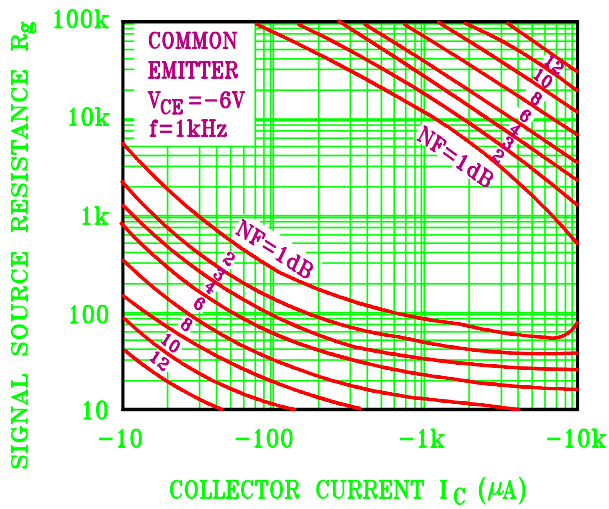
$h_{FE} - I_C$



h PARAMETER - I_E



NF - R_g, I_C



$C_{ob} - V_{CB}$

